

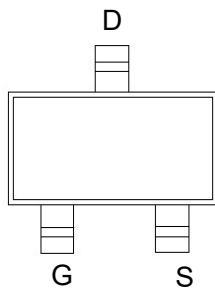
-100V/-3A P-Channel MOSFET

Features

- Split gate trench MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching
- Excellent stability and uniformity

Application

- Battery protection
- Load switch
- Power management

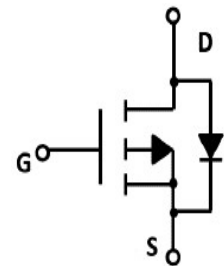


Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-100V	350mΩ@-10V	-3A
	400mΩ@-4.5V	



SOT-23-3L top view



Schematic diagram



Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage		-100	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_c=25^\circ\text{C}$	-3	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$	-10	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	-3	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	1.8	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		315	°C/W

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-100V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-3A	--	280	350	mΩ
		V _{GS} =-4.5V, I _D =-1A	--	315	400	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-50V, V _{GS} =0V, f=1MHz	--	740	--	pF
C _{OSS}	Output Capacitance		--	30	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	20.5	--	pF
Q _g	Total Gate Charge	V _{DS} =-50V, I _D =-6A, V _{GS} =-10V	--	15	--	nC
Q _{gs}	Gate Source Charge		--	2	--	nC
Q _{gd}	Gate Drain Charge		--	2.5	--	nC
8						
t _{d(on)}	Turn-on Delay Time	V _{DS} =-50V, I _D =-3A, V _{GS} =-10V, R _G =3Ω	--	8	--	nS
t _r	Turn-on Rise Time		--	6.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	29	--	nS
t _f	Turn-Off Fall Time		--	8.5	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=-3A	--	--	-1.2	V

Typical Operating Characteristics

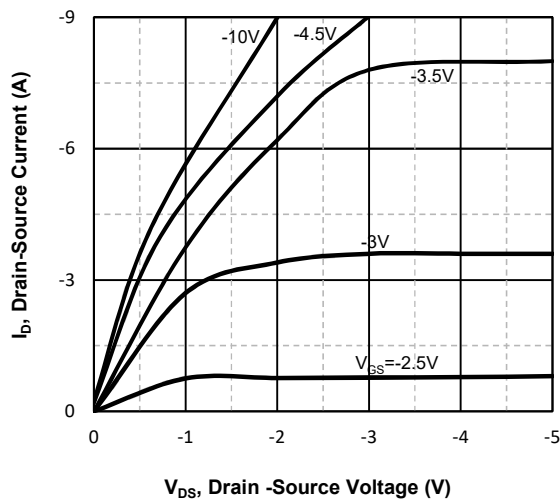


Fig1. Typical Output Characteristics

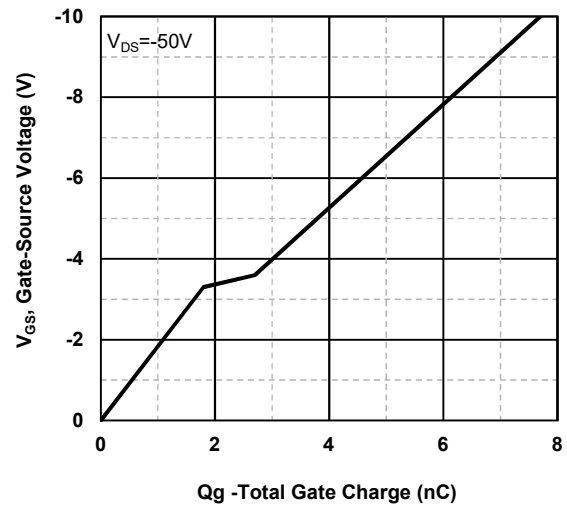


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

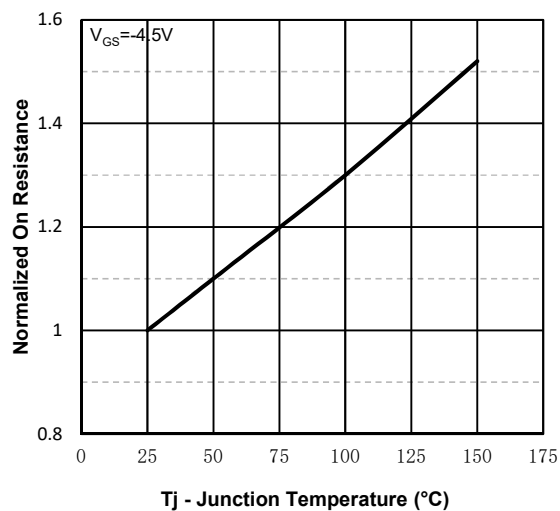


Fig3. Normalized On-Resistance Vs. Temperature

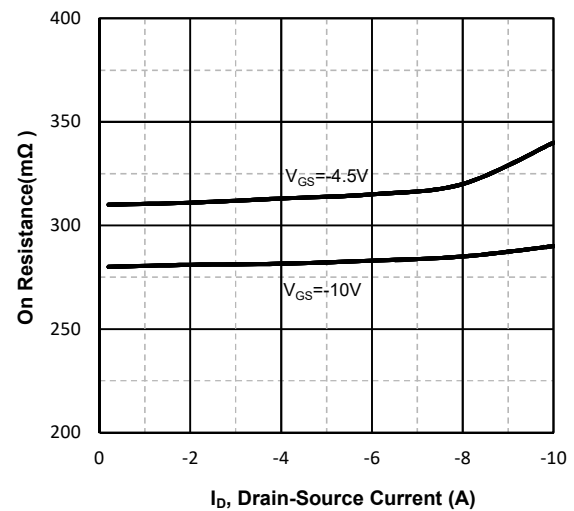


Fig4. On-Resistance Vs. Drain-Source Current

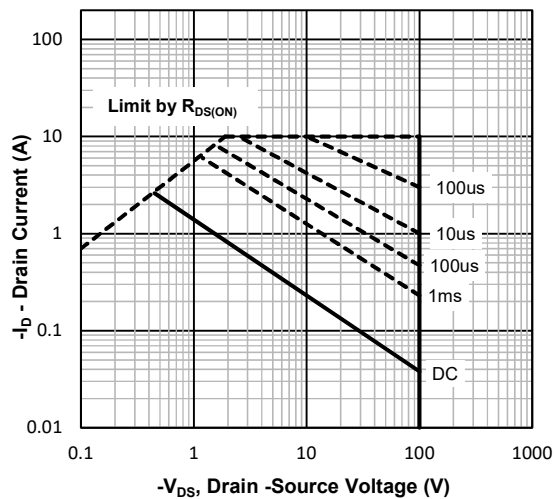


Fig5. Maximum Safe Operating Area

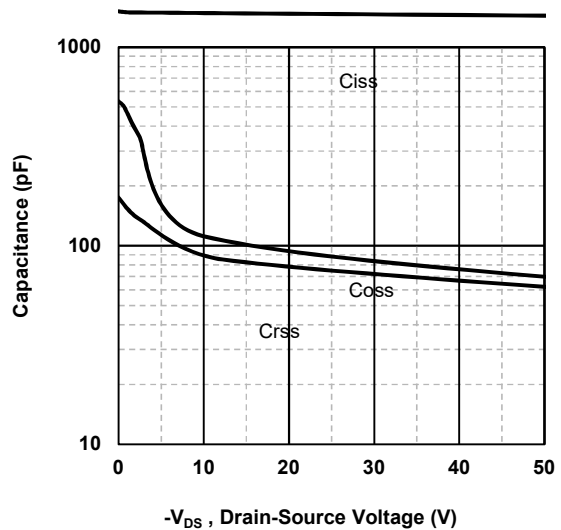
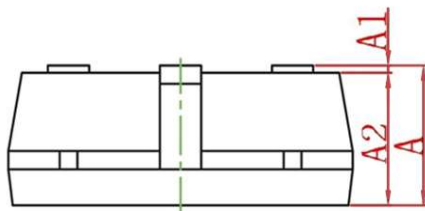
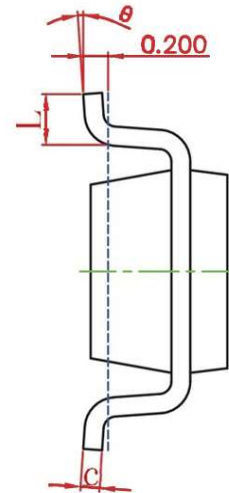
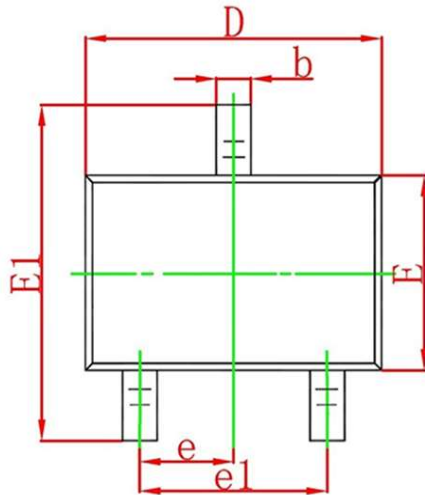


Fig6 Typical Capacitance Vs. Drain-Source

SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.042	0.050
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.042	0.046
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.112	0.120
E	1.500	1.700	0.060	0.068
E1	2.650	2.950	0.106	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°